WHAT IS CLAIMED IS:

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1. A method for preparing multicrystalline substrates as handling wafers for subsequent bonding to device layer materials, the method comprising the steps of:

providing an initial multicrystalline substrate;

polishing the multicrystalline substrate to reduce surface roughness to about 5 nm;

forming a filler layer overlying the face of the substrate to a predetermined thickness, the filler layer comprising a surface that is substantially free from indications of the multicrystalline arrangement; and

further polishing the surface of the filler layer to form a substantially smooth upper surface on the substrate,

wherein the substantially smooth upper surface is characterized by a surface roughness of twenty Angstroms or less.

2. The method of claim 1, wherein the initial substrate is selected from a polycrystalline silicon wafer, a glass substrate, a ceramic substrate, an organic film, a metal substrate, and an amorphous wafer.

3. The method of claim 1, wherein the initial substrate has a typical crystalline dimension of about 0.5 to 10 millimeters in size.

4. The method of claim 1, wherein the filler layer is selected from a CVD oxide, and a polycrystalline silicon.

5. The method of claim 1, wherein the filler layer is removed to a thickness of one half or more of the predetermined thickness.

6. The method of claim 1, wherein the filler layer is a polycrystalline silicon, the polycrystalline being formed using a low pressure chemical deposition technique.

7. The method of claim 1, wherein the filler layer is chosen from the group consisting of an insulating layer andor a composite layer.

8. The method of claim 1, wherein the surface roughness is five Angstroms or less.

A1

9. The method of claim 1, wherein the filler layer is made by a chemical deposition process or a sputtering process.

10. The method of claim 1, wherein the substrate is a ground substrate or unpolished substrate.

11. The method of claim 1, wherein the polishing process is a chemical mechanical polishing technique comprising:

applying a mechanical fine-grinding step;

applying a rough polishing step using a weakly alkaline slurry;

changing the composition of the slurry by feeding a neutral polishing slurry to the polishing pad and gradually reducing supply of rough polishing slurry; and

wherein surface roughness after polishing is 0.5 nm or less.

12. The method of claim 1, wherein the polishing process is a chemical mechanical polishing comprising:

applying a mechanical fine-grinding step;

applying a rough polishing step using a weakly alkaline slurry;

adding TMAH to the slurry to adjust the alkalinity of the slurry for increased removal rates while maintaining material removal rates relatively constant between various grain regions of the substrate; and

effecting a controlled transition to a second slurry composition to obtain microscopically smooth surfaces;

wherein surface roughness after polishing is 0.5 nm or less.

13. The method of claim 1, wherein the polishing process is a double-sided chemical mechanical polishing technique comprising:

applying a mechanical fine-grinding step;

applying a rough polishing step using a weakly alkaline slurry;

changing the composition of the slurry by feeding a neutral polishing slurry to the polishing pad and gradually reducing supply of rough polishing slurry; and

wherein surface roughness after polishing is twenty Angstroms or less.

A1

14. The method of claim 1, wherein the polishing process is a double-sided chemical mechanical polishing technique in which polishing is done on a double-sided polishing machine to polish front and back sides of the substrate simultaneously, comprising:

applying a mechanical fine-grinding step;

applying a rough polishing step using a weakly alkaline slurry;

adding TMAH to the slurry to adjust the alkalinity of the slurry for increased removal rates while maintaining material removal rates relatively constant between various grain regions of the substrate;

effecting a controlled transition to a second slurry composition to obtain microscopically smooth surfaces;

wherein the front and back side each achieve a flatness of 0.5 micron or less; and

the front side achieves a roughness of 0.5 nm or less.

15. Electronic devices made from bonded assemblies prepared using the method of claim 1.

16. Micro-Electro-Mechanical Structures (MEMS) made from bonded assemblies prepared using the method of claim 1.

17. Micro-Opto-Electro-Mechanical Structures (MOEMS) made from bonded assemblies prepared using the method of claim 1.

18. A method for polishing substrates, the method comprising steps of:

applying a rough polishing step using a weakly alkaline slurry;

changing the composition of the slurry by feeding a neutral polishing slurry to the polishing pad and gradually reducing supply of rough polishing slurry; and

wherein surface roughness after polishing is 0.5 nm or less.

19. The method of claim 18, wherein the polishing is performed on a double-sided polishing machine to polish front and back sides of said substrate simultaneously.

20. Electronic devices made from bonded assemblies prepared using the method of claim 18.

21. Micro-Electro-Mechanical Structures (MEMS) made from bonded assemblies prepared using the method of claim 18.

22. Micro-Opto-Electro-Mechanical Structures (MOEMS) made from bonded assemblies prepared using the method of claim 18.

A1

23. A method for detection of hidden bonding flaws in multiple bonded wafers, the method comprising steps of:

transmitting infrared radiation through a first side of a multiple bonded wafer sample;

receiving the scattered infrared radiation exiting from a second side of said sample, said second said being opposite from said first side; and

converting said received radiation into an electronic signal in which defects appear as local maxima of said signal.